Digital IC Design and Architecture

MOS Inverter Static Characteristics

IDEAL INVERTER VOLTAGE TRANSFER CHARTERISTIC (VTC)

ACTUAL INVERTER VOLTAGE TRANSFER 3 **CHARTERISTIC (VTC)**

NOISE IMMUNITY AND NOISE MARGINS

 V_{OH} -> max output voltage when output is "1" V_{OL} -> min output voltage when output is "0" V_{H} -> max input voltage which can be interpreted as "0" V_{th} -> min input voltage which can be interpreted as "1"

NOISE IMMUNITY AND NOISE MARGINS V_{OH} -> max output voltage when output is "1" $V_{\text{or}} \rightarrow$ min output voltage when output is "0" V_{H} -> max input voltage which can be interpreted as "0" $\rm V_{\rm IH}$ -> min input voltage which can be interpreted as "1" $\rm V_{\rm DD}$ $\frac{V_{\text{out}}}{V_{\text{OH}}}$ NM_{H} 4 $NM_{H} = V_{OH} - V_{IH}$ Transition Region $NM_{L} = V_{H} - V_{OL}$ NM_{τ} JUSTIFICATION FOR V_{H} , V_{H} . LET: $V_{\text{out}} = f(V_{\text{in}})$, $V_{\text{out}}' = f(V_{\text{in}} + \Delta V_{\text{noise}})$ Using first-order Taylor series $V_{\text{out}} = f(V_{\text{in}}) + \frac{dV_{\text{out}}}{dV_{\text{in}}} \Delta V_{\text{noise}} + H \cdot Q \cdot \text{term}$ expansionPerturbed Output = Nominal Output + Gain x Ext. Perturbation

FIVE CRITICAL VOLTAGES: V_{OL} , V_{OL} , V_{L} , V_{L} , V_{L} , V_{th} determine:

- --> DC Output Voltage Behavior
- --> Noise Margins
- --> Width and Location of Transition Region

POWER DISSIPATION AND DIE AREA

Power Dissipation -> HEAT

$$
\mathbf{T_j} = \mathbf{T_a} + \boldsymbol{\Theta}\,\mathbf{P}
$$

 $P \rightarrow P_{DC}$, $P_{dynamic}$

 T_i -> junction Temp
 T_a -> ambient Temp Θ -> Thermal Resistance P -> Power Dissipated

6

$$
P_{DC} = V_{DD} I_{DC}
$$

ASSUME: $V_{in} = "1" 50\% \text{ of Op Time}, "0" 50\% \text{ of Op Time}$

$$
P_{DC} = \frac{V_{DD}}{2} [I_{DC}(V_{in} = "0") + I_{DC}(V_{in} = "1")]
$$

DIE AREA --> MIN W x L and routing \rightarrow limited by design rules

Digital IC Design and Architecture

CMOS Inverter

CMOS Inverter Circuit

CMOS Inverter Circuit

Input Voltage (V)

CALCULATE V_{OL}

CALCULATE V_{OL}

CALCULATE V_{OL}

$$
\begin{aligned} &I_{Dp} = I_{Dn} \\ &\frac{k_{n}^{'}\left(W\right)}{2}\Big(V_{GSn}-V_{T0\;n}\Big)^{2} = \frac{k_{p}^{'}\left(W\right)}{2}\Bigg[2\Big(V_{GSp}-V_{T0\;p}\Big)V_{DSp}-V_{DSp}^{2}\Bigg] \end{aligned}
$$

$$
V_{GSn} = V_{in'} V_{GSp} = V_{in} - V_{DD'} V_{DSp} = V_{out} - V_{DD}
$$

\n
$$
\frac{k_n'}{2} \left(\frac{W}{L}\right)_n \left(V_{in} - V_{Ton}\right)^2
$$

\n
$$
= \frac{k_p'}{2} \left(\frac{W}{L}\right)_p \left[2\left(V_{in} - V_{DD} - V_{Top}\right)\left(V_{out} - V_{DD}\right) - \left(V_{out} - V_{DD}\right)^2\right]
$$

- nMOS is in saturation region - pMOS is in linear region

 χ^2

$$
\begin{aligned} &I_{Dp} = I_{Dn} \\ &\frac{k_{n}^{'}\left(W\right)}{2}\Big(V_{G S n} - V_{T\,0\;n} \Big)^{2} = \frac{k_{p}^{'}\left(W\right)}{2}\Bigg[2\Big(V_{G S p} - V_{T\,0\;p} \Big) V_{D S p} - V_{D S p}^{2}\Bigg] \end{aligned}
$$

$$
V_{GSn} = V_{in'} V_{GSp} = V_{in} - V_{DD'} V_{DSp} = V_{out} - V_{DD}
$$

\n
$$
\frac{k_n'}{2} \left(\frac{W}{L}\right)_n \left(V_{in} - V_{T0n}\right)^2
$$

\n
$$
= \frac{k_p'}{2} \left(\frac{W}{L}\right)_p \left[2\left(V_{in} - V_{DD} - V_{T0p}\right)\left(V_{out} - V_{DD}\right) - \left(V_{out} - V_{DD}\right)\right]
$$

$$
\frac{k_{n}}{2} \left(\frac{W}{L} \right)_{n} \left(V_{in} - V_{Ton} \right)^{2}
$$
\n
$$
= \frac{k_{p}}{2} \left(\frac{W}{L} \right)_{p} \left[2 \left(V_{in} - V_{DD} - V_{Top} \right) \left(V_{out} - V_{DD} \right) - \left(V_{out} - V_{DD} \right)^{2} \right]
$$
\n
$$
= \frac{k_{p}}{2} \left(\frac{W}{L} \right)_{p} \left[2 \left(V_{in} - V_{DD} - V_{Top} \right) \left(V_{out} - V_{DD} \right) - \left(V_{out} - V_{DD} \right)^{2} \right]
$$
\n
$$
= k_{n} \left(\frac{W}{L} \right)_{n} \left(V_{in} - V_{Ton} \right) = k_{p} \left(\frac{W}{L} \right)_{p} \left[\left(V_{out} - V_{DD} \right) + \left(V_{in} - V_{DD} - V_{Top} \right) \frac{dV_{out}}{dV_{in}} \left(-1 \right)^{2} \right]
$$
\n
$$
= \left(V_{out} - V_{DD} \right) \frac{dV_{out}}{dV_{in}} \left(\frac{-1}{L} \right)
$$
\n
$$
= k_{n} \left(\frac{W}{L} \right)_{n} \left(V_{in} - V_{Ton} \right) = k_{p} \left(\frac{W}{L} \right)_{p} \left[2 V_{out} - V_{in} + V_{Top} - V_{DD} \right]
$$
\n(5.59)

SOLVING FOR V_{IL}

where $k_R = \frac{k_n (W/L)_n}{k_n (W/L)_p}$ $\frac{2(V_{\text{out}} + V_{\text{Top}} - V_{\text{DD}} + k_{\text{R}}V_{\text{Top}})}{1 + k_{\text{R}}}$ (5.62) SOLVE Eqs (5.59) and (5.62) for V_{out} and V_{IL}

$$
I_{Dp} = I_{Dn}
$$
\n
$$
\frac{k_n^{'}(W)}{2} \left[2(V_{GSn} - V_{T0n}) V_{DSn} - V_{DSn}^2 \right] = \frac{k_p^{'}(W)}{2} \left(V_{GSp} - V_{T0p} \right)^2
$$
\n
$$
V_{GSn} = V_{in'} V_{DSn} = V_{out'} V_{GSp} = V_{in} - V_{DD}
$$
\n
$$
\frac{k_n^{'}(W)}{2} \left(\frac{W}{L} \right)_n \left[2(V_{in} - V_{T0n}) V_{out} - V_{out}^2 \right] = \frac{k_p^{'}(W)}{2} \left(\frac{W}{L} \right)_p \left(V_{in} - V_{DD} - V_{T0p} \right)^2
$$

 $\rm V_{out}$

- nMOS is in linear region
- pMOS is in saturation region

$$
\frac{k_{n}^{'}(W)}{2}\left[\frac{2(V_{in} - V_{Ton})V_{out} - V_{out}^{2}}{2}\right] = \frac{k_{p}^{'}(W)}{2}\left(V_{in} - V_{DD} - V_{Top}\right)^{2}
$$
(5.64)

$$
\begin{aligned} &\quad \ \ \, \text{DIFFERENTIATING wrt } V_{in} \\ &\quad \ \ \, k_n \bigg(\frac{W}{L}\bigg)_n \bigg[\big(y_{in}^\prime - V_{To\ n}\big) \frac{dV_{out}^\prime}{dV_{in}} + V_{out} - V_{out} \frac{dV_{out}^\prime}{dV_{in}}\bigg] = k_p^{'} \bigg(\frac{W}{L}\bigg)_p \big(y_{in}^\prime - V_{DD} - V_{To\ p}\big) \end{aligned}
$$

$$
k^{'}_{n}\bigg(\frac{W}{L}\bigg)_{n}\big[-V_{IH}+V_{T0n}+2\,V_{out}\big] \!= k^{'}_{p}\bigg(\frac{W}{L}\bigg)_{p}\Big(V_{IH}-V_{DD}-V_{T0p}\Big)
$$

SOLVING FOR $\rm V_{\rm IH}$

$$
V_{IH} = \frac{V_{DD} + V_{Top} + k_R (2(V_{out}) + V_{Top})}{1 + k_R}
$$

where
$$
k_R = \frac{k_n (W/L)_n}{k_p (W/L)_p}
$$
 (5.67)

SOLVE Eqs. (5.64) and (5.67) for V_{out} and V_{IH}

$$
\begin{array}{l} {I_{Dp} = I_{Dn}} \\ {\frac{k_{{n}}^{'}}{2}{{\left({\frac{W}{L}} \right)}_n}{\left({{V_{GSn}}\!-\!{V_{T0}}_n} \right)}^2} = \frac{{{k^{'}}_p}}{2}{{\left({\frac{W}{L}} \right)}_p}{\left({{V_{GSp}}\!-\!{V_{T0}}_p} \right)}^2} \end{array}
$$

$$
V_{GSn} = V_{in'} V_{GSp} = V_{in} - V_{DD}
$$

$$
\frac{k_n'}{2} \left(\frac{W}{L}\right)_n \left(V_{in} - V_{To n}\right)^2 = \frac{k_p'}{2} \left(\frac{W}{L}\right)_p \left(V_{in} - V_{DD} - V_{To p}\right)^2
$$

- nMOS is in saturation region

pMOS is in saturation region

$$
V_{GSn} = V_{in'} V_{GSp} = V_{in} - V_{DD}
$$

$$
\frac{k_n'}{2} \left(\frac{W}{L}\right)_n \left(V_{in} - V_{Ton}\right)^2 = \frac{k_p'}{2} \left(\frac{W}{L}\right)_p \left(V_{in} - V_{DD} - V_{Top}\right)^2
$$

$$
\frac{k_n}{2} \left(\frac{W}{L}\right)_n \left(V_{in} - V_{Ton}\right)^2 = \frac{k_p}{2} \left(\frac{W}{L}\right)_p \left(V_{in} - V_{DD} - V_{Top}\right)^2
$$

SOLVING for $V_{th} = V_{in}$

$$
V_{in} = V_{th} = \frac{V_{Ton} + \sqrt{\frac{1}{k_R}} \left(V_{DD} + V_{Top}\right)}{\left(1 + \sqrt{\frac{1}{k_R}}\right)}
$$

A) B O D E

RECALL THAT $V_{th} = V_{in} = V_{out}$ 37

POWER SUPPLY CURRENT VS V_{IN}

$$
I_{D} = 0, V_{in} < V_{T0n}
$$

\n
$$
I_{D} = 0, V_{in} > V_{DD} + V_{T0p}
$$

\n
$$
I_{D} = MAX, V_{in} = V_{th}
$$

Almost all power is dissipated during the switching!

$$
DESIGN OF CMOS INVERTERS
$$

\n
$$
V_{in} = V_{th} = \frac{V_{Ton} + \sqrt{\frac{1}{k_R}}(V_{DD} + V_{Top})}{\left(1 + \sqrt{\frac{1}{k_R}}\right)}
$$

\nSOLVING FOR k_R
\n
$$
k_R = \left(\frac{V_{DD} + V_{Top} - V_{th}}{V_{th} - V_{Ton}}\right)^2
$$

\nFOR IDEAL INVERTER $V_{th} = \frac{1}{2}V_{DD}$

 $(K_R)_{\text{ideal}} = \left(\frac{0.5 V_{\text{DD}} + V_{\text{T0p}}}{0.5 V_{\text{DD}} - V_{\text{T0p}}}\right)^2$ IF $V_{T0} = V_{T0n} = -V_{T0p}$ => (k_R) symmetric = 1

$$
k_R = \frac{k_n^{'}(W/L)_n}{k_p^{'}(W/L)_p} = \frac{\mu_n C_{ox}(W/L)_n}{\mu_p C_{ox}(W/L)_p} = \frac{\mu_n (W/L)_n}{\mu_p (W/L)_p}
$$

FOR SYMMETRIC INVERTER $V_{T0} = V_{T0n} = -V_{T0p}$ (k_R) symmetric = 1

$$
\frac{(W/L)_n}{(W/L)_p} = k_R \frac{\mu_P}{\mu_n} \longrightarrow \frac{k_R - 1}{(W/L)_p} \frac{(W/L)_n}{(\mu_n)} = \frac{\mu_P}{\mu_n}
$$
\n
$$
\frac{(W/L)_n}{(W/L)_p} = \frac{\mu_p}{\mu_n} = \frac{230 \text{ cm}^2/\text{Vs}}{580 \text{ cm}^2/\text{Vs}} \longrightarrow \frac{(W/L)_p}{(W/L)_p} = 2.5 (W/L)_n
$$
\n
$$
V_{\text{IL}} = \frac{1}{8} (3 V_{\text{DD}} + 2 V_{\text{T0}}) \text{ solve eqs. (5.59) and (5.62)}
$$
\n
$$
V_{\text{IH}} = \frac{1}{8} (5 V_{\text{DD}} - 2 V_{\text{T0}}) \text{ solve eqs. (5.64) and (5.67)}
$$
\n
$$
\frac{\text{NOTE: } V_{\text{IL}} + V_{\text{LI}}}{\text{NOTE: } V_{\text{IL}} + V_{\text{HI}} = V_{\text{DD}}}
$$
\n
$$
\frac{\text{NML}}{\text{NM}_{\text{L}} = V_{\text{DI}} - V_{\text{IH}} = V_{\text{DD}} - V_{\text{IH}} = (3/8) V_{\text{DD}} + (2/8) V_{\text{T0}}}{\text{NM}_{\text{L}} = V_{\text{IL}} - V_{\text{OL}} = V_{\text{IL}} = (3/8) V_{\text{DD}} + (2/8) V_{\text{T0}}}
$$

VTC for three CMOS inverters with different nMOS-pMOS ratios

POWER DISSIPATION CONSIDERATIONS

$$
P_{DC} = \frac{V_{DD}}{2} [I_{DC}(V_{in} = "0") + I_{DC}(V_{in} = "1")] = \frac{P(V_{in} = 0) + P(V_{in} = 1)}{2}
$$

WHEN V_{in} = V_{OL}: $I_{L} = I_{D} = 0 \implies P(V_{in} = 0) = 0$
WHEN V_{in} = V_{OH}: $I_{L} = I_{D} = 0 \implies P(V_{in} = 1) = 0$
 $P_{DC} = 0$

Minimum Area MOS Transistor Layouts

DIE AREA CONSIDERATIONS V_{in} COLOR LEGEND n-Well $n⁺$ Polysilicon p^* Metal 1 $\rm V_{\rm DD}$ **GND** V Contact/via out V_{in} **GND** V_{DD} V out

Digital IC Design and Architecture

Resistive Load Inverter

RESISTIVE-LOAD INVERTER

$$
CUTOFF: V_{in} = V_{GS} < V_{T0,n'} I_D = 0
$$
\nI INFAR: V = V > V

$$
V_{\text{L}} = V_{\text{cs}} \ge V_{\text{T0,n'}}V_{\text{out}} = V_{\text{DS}} \le V_{\text{in}} - V_{\text{t0,n}}I_{\text{D}} = \frac{k_{\text{n}}}{2} [2(V_{\text{in}} - V_{\text{T0,n}}) V_{\text{out}} - V_{\text{out}}^2]
$$

SATURATION:

$$
V_{in} = V_{GS} \ge V_{T0,n}
$$

\n
$$
V_{out} = V_{DS} > V_{in} - V_{T0,n}
$$

\n
$$
I_{D} = \frac{k_{n}}{2} (V_{in} - V_{T0,n})^{2}
$$

Units

$$
k_{n} = \left(\frac{cm^{2}}{V \sec}\right)\left(\frac{F}{cm^{2}}\right) = \left(\frac{cm^{2}}{V \sec}\right)\left(\frac{C}{V \cosh^{2}}\right)
$$

$$
= \left(\frac{C/\sec}{V^{2}}\right) = \frac{A}{V^{2}}
$$

Let (for hand calculations) $\lambda = 0$

Where: $k_n = \mu_n C_{ox} \frac{W}{L}$ **RESISTOR R.:**

$$
I_L = \frac{V_{DD} - V_{out}}{R_L}
$$

CALCULATION OF V_{OH} : (A) $V_{\text{out}} = V_{\text{DD}} - R_{\text{L}} I_{\text{L}}$ V_{in} < $V_{T0,n}$ => nMOS Cut-off $I_D = I_L = 0 \implies V_{OH} = V_{DD}$

$$
\frac{V_{DD}}{R_{L}}\begin{bmatrix} 1 & 0 \\ 0 & V_{OL} \end{bmatrix}^{10} + \frac{V_{DD}}{R_{L}}V_{L} & I_{L} = \frac{V_{DD} - V_{out}}{R_{L}} \qquad \frac{V_{DD}}{R_{L} \geq 1}V_{L} \\ V_{in} = V_{GS} \frac{V_{out}}{V_{in}} \begin{bmatrix} 1 & 0 \\ 0 & V_{OL} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{OL} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{out} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{out} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{out} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{out} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{out} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{out} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{out} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{out} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{out} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{out} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{out} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{out} \end{bmatrix}^{10} + \frac{V_{out}}{V_{out}} \begin{bmatrix} 1 & 0 \\ 0 & V_{out} \end
$$

$$
I_{L} = I_{D} \longrightarrow \frac{V_{DD} - V_{out}}{R_{L}} = \frac{K_{n}}{2} \Big[2(V_{in} - V_{T0,n}) V_{out} - V_{out}^{2} \Big]
$$

Differentiate wrt to V_{in'} i.e.
\n
$$
-\frac{1}{R_{L}}\frac{dV_{out}^{2}}{dV_{in}} = \frac{k_{n}}{2} \left[2(V_{in}^{2} - V_{To,n}) \frac{dV_{out}^{2}}{dV_{in}} + 2 V_{out} - 2 V_{out} \frac{dV_{out}^{2}}{dV_{in}} \right]
$$
\n
$$
V_{in} = V_{To,n} + 2 V_{out} - \frac{1}{k_{n}R_{L}}
$$

CALCULATION OF V_{1H}:
\n
$$
\begin{aligned}\n&\text{Find } V_{out}(V_{in} = V_{H}):\n\\&\text{Find } V_{out}(V_{in} = V_{H}):\n\\&\text{where } V_{H} = \frac{k_{n}}{2} [2(V_{H} - V_{To,n}) V_{out} - V_{out}^{2}] \\
&\text{where } V_{H} = V_{To,n} + 2V_{out} - \frac{1}{k_{n}R_{L}} \\
&\text{where } V_{H} = V_{To,n} + 2V_{out} - \frac{1}{k_{n}R_{L}} \\
&\text{where } V_{H} = \frac{1}{2} [2(V_{To,n} + 2V_{out} - \frac{1}{k_{n}R_{L}} - V_{To,n}^{2}) V_{out} - V_{out}^{2}] \\
&\text{where } V_{H} = \frac{k_{n}}{2} [2(V_{To,n} + 2V_{out} - \frac{1}{k_{n}R_{L}} - V_{To,n}^{2}) V_{out} - V_{out}^{2}] \\
&\text{where } V_{H} = \frac{1}{2} [3V_{out}^{2} - \frac{2V_{out}}{k_{n}R_{L}}] \\
&\text{where } V_{H} = \frac{1}{2} [3V_{out}^{2} - \frac{1}{k_{n}R_{L}} - V_{To,n}^{2}] \\
&\text{where } V_{H} = \frac{1}{2} [3V_{out}^{2} - \frac{1}{k_{n}R_{L}} - \frac{1}{k_{n}R_{L}}] \\
&\text{where } V_{H} = \frac{1}{2} [2(V_{H} - V_{To,n}) V_{out} - V_{out}^{2}] \\
&\text{where } V_{H} = \frac{1}{2} [2(V_{H} - V_{To,n}) V_{out} - V_{out}^{2}] \\
&\text{where } V_{H} = \frac{1}{2} [2(V_{H} - V_{To,n}) V_{out} - V_{out}^{2}] \\
&\text{where } V_{H} = \frac{1}{2} [2(V_{H} - V_{To,n}) V_{out} - V_{out}^{2}] \\
&\text{where } V_{H} = \frac{1}{2} [2(V_{H} - V_{To,n}) V_{out} - V_{out}^{2}] \\
&\text{where } V_{H} = \frac{1}{2} [2(V_{H} - V_{To,n}) V_{out} - V_{out}^{2}] \\
&\text{where } V_{H} = \frac{1}{2} [2
$$

CALCULATION OF V_{th}:
\n
$$
V_{in} = V_{out} = V_{th} \implies V_{DS} = V_{GS} > V_{GS} - V_{T0,n} \implies B
$$
\n
$$
I_{L} = I_{D} \implies \frac{V_{DD} - V_{out}^{V_{th}}}{R_{L}} = \frac{k_{n}}{2} (V_{dn}^{V_{th}} - V_{T0,n})^{2}
$$
\n
$$
\frac{V_{DD} - V_{th}}{R_{L}} = \frac{k_{n}}{2} (V_{th} - V_{T0,n})^{2}
$$
\n
$$
V_{th}^{2} - 2 \left(V_{T0,n} - \frac{1}{k_{n}R_{L}}\right) V_{th} + V_{T0,n}^{2} - \frac{2V_{DD}}{k_{n}R_{L}} = 0
$$
\n
$$
V_{th} = V_{T0,n} - \frac{1}{k_{n}R_{L}} \pm \sqrt{\left(V_{T0,n} - \frac{1}{k_{n}R_{L}}\right)^{2} + \frac{2V_{DD}}{k_{n}R_{L}} - V_{T0,n}^{2}}
$$

POWER DISSIPATION - RESISTIVE LOAD INVERTER 16

$$
P_{DC} = \frac{V_{DD}}{2} [I_{DC}(V_{in} = "0") + I_{DC}(V_{in} = "1")]
$$

WHEN $V_{in} = V_{OL}$: DRIVER nMOS in CUT-OFF $I_{\text{L}} = I_{\text{D}} = 0 \implies P(V_{\text{in}} = 0) = 0$

WHEN V_{in} = V_{OH}:

\n
$$
I_{DC}(V_{in} = "T') = I_{L} = I_{D} = \frac{V_{DD} - V_{OL}}{R_{L}}
$$
\n
$$
P(V_{in} = "T') = \frac{V_{DD}}{2} \frac{V_{DD} - V_{OL}}{R_{L}}
$$

$$
P_{DC}(\text{average}) = \frac{V_{DD} V_{DD} - V_{OL}}{2} R_{L}
$$

$$
Q\n\nR\n\n
$$
R\n\nV00t
$$
\n
$$
R\n\n
$$
V_{out}
$$
\n
$$
R\n\n
$$
V_{out}
$$
\n
$$
R\n\n
$$
V_{out}
$$
\n
$$
V_{out}
$$
\n
$$
V_{out}
$$
\n
$$
V_{out}
$$
$$
$$
$$
$$

Two examples of resistive load inverter layout are shown below:

Figure 5.10. Sample layout of resistive-load inverter circuits with (a) diffused resistor and (b) undoped polysilicon resistor. $\mathbb{R}^n \times \mathbb{R}^n$

Digital IC Design and Architecture

Saturated Enhancement Load Inverter

S

LOAD: $V_{GS,L} = V_{DS,L} \Rightarrow V_{DS,L} > V_{GS,L}$ - $V_{T,L}$ SAT cond. is ALWAYS SATISFIED

$$
I_{L} = \frac{k_{n}^{'}(W)}{2} \left(\frac{W}{L} \right)_{L} \left(V_{GS,L} - V_{T.L} \right)^{2} = \frac{k_{n}^{'}(W)}{2} \left(\frac{W}{L} \right)_{L} \left(V_{DD} - V_{out} - V_{T.L} \right)^{2}
$$

- Saturated Enhancement Load Inverters require relatively high stand-by DC power dissipation
- Because of this high stand-by DC power dissipation the Enhancement-load nMOS inverters are not used in any large-scale digital applications

Textbook examples to be reviewed:

Examples 5.1 and 5.2 – Resistive Load Inverter

Example 5.4 – nMOS with pMOS Load Inverter